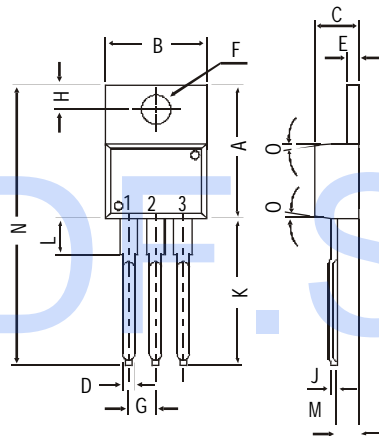
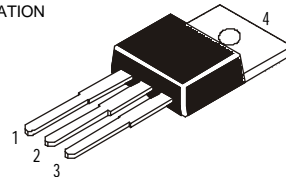


TO-220 Plastic Package

**2N6486, 2N6487, 2N6488
2N6489, 2N6490, 2N6491**

*2N6486, 6487, 6488 NPN PLASTIC POWER TRANSISTORS
2N6489, 6490, 6491 PNP PLASTIC POWER TRANSISTORS
General Purpose Amplifier and Switching Applications*

PIN CONFIGURATION
1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR



| DIM | MIN. | MAX. |
|-----|-------|-------|
| A | 14.42 | 16.51 |
| B | 9.63 | 10.67 |
| C | 3.56 | 4.83 |
| D | | 0.90 |
| E | 1.15 | 1.40 |
| F | 3.75 | 3.88 |
| G | 2.29 | 2.79 |
| H | 2.54 | 3.43 |
| J | | 0.56 |
| K | 12.70 | 14.73 |
| L | 2.80 | 4.07 |
| M | 2.03 | 2.92 |
| N | | 31.24 |
| O | DEG 7 | |

All dimensions in mm.

ABSOLUTE MAXIMUM RATINGS

| | | 6486 | 6487 | 6488 | |
|--|------------------|-------------|-------------|-------------|------------|
| | | 6489 | 6490 | 6491 | |
| Collector-base voltage (open emitter) | V_{CBO} max. | 50 | 70 | 90 | V |
| Collector-emitter voltage (open base) | V_{CEO} max. | 40 | 60 | 80 | V |
| Collector current | I_C max. | | 15 | | A |
| Total power dissipation up to $T_C = 25^\circ C$ | P_{tot} max. | | 75 | | W |
| Junction temperature | T_j max. | | 150 | | $^\circ C$ |
| Collector-emitter saturation voltage $I_C = 5 A; I_B = 0.5 A$ | V_{CEsat} max. | | 1.3 | | V |
| D.C. current gain $I_C = 5 A; V_{CE} = 4 V$ | h_{FE} min. | | 20 | | |
| | | | max. | 150 | |

RATINGS (at $T_A=25^\circ C$ unless otherwise specified)

| | | 6486 | 6487 | 6488 | |
|---------------------------------------|----------------|-------------|-------------|-------------|---|
| | | 6489 | 6490 | 6491 | |
| Collector-base voltage (open emitter) | V_{CBO} max. | 50 | 70 | 90 | V |
| Collector-emitter voltage (open base) | V_{CEO} max. | 40 | 60 | 80 | V |
| Emitter-base voltage (open collector) | V_{EBO} max. | | 5.0 | | V |

**2N6486, 2N6487, 2N6488
2N6489, 2N6490, 2N6491**

| | | | | |
|--|-----------|------|-------------|-------------------|
| Collector current | I_C | max. | 15 | A |
| Base current | I_B | max. | 5.0 | A |
| Total power dissipation up to $T_C = 25^\circ\text{C}$ | P_{tot} | max. | 75 | W |
| Derate above 25°C | | max. | 0.6 | $W^\circ\text{C}$ |
| Total power dissipation up to $T_A = 25^\circ\text{C}$ | P_{tot} | max. | 1.8 | W |
| Derate above 25°C | | max. | 0.014 | $W^\circ\text{C}$ |
| Junction temperature | T_j | max. | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | | -65 to +150 | $^\circ\text{C}$ |

THERMAL RESISTANCE

| | | | | |
|--------------------------|---------------|--|------|--------------------|
| From junction to ambient | $R_{th\ j-a}$ | | 70 | $^\circ\text{C/W}$ |
| From junction to case | $R_{th\ j-c}$ | | 1.67 | $^\circ\text{C/W}$ |

CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified

**6486 6487 6488
6489 6490 6491**

| | | | | |
|---|------------------|------|-----|---------------------|
| Collector cutoff current | | | | |
| $I_B = 0; V_{CE} = 20\text{ V}$ | I_{CEO} | max. | 1.0 | - - mA |
| $I_B = 0; V_{CE} = 30\text{ V}$ | I_{CEO} | max. | - | 1.0 - mA |
| $I_B = 0; V_{CE} = 40\text{ V}$ | I_{CEO} | max. | - | - 1.0 mA |
| $V_{EB(off)} = 1.5\text{ V}; V_{CE} = 45\text{ V}$ | I_{CEX} | max. | 500 | - - μA |
| $V_{EB(off)} = 1.5\text{ V}; V_{CE} = 65\text{ V}$ | I_{CEX} | max. | - | 500 - μA |
| $V_{EB(off)} = 1.5\text{ V}; V_{CE} = 85\text{ V}$ | I_{CEX} | max. | - | - 500 μA |
| $V_{EB(off)} = 1.5\text{ V}; V_{CE} = 40\text{ V}; T_C = 150^\circ\text{C}$ | I_{CEX} | max. | 5.0 | - - mA |
| $V_{EB(off)} = 1.5\text{ V}; V_{CE} = 60\text{ V}; T_C = 150^\circ\text{C}$ | I_{CEX} | max. | - | 5.0 - mA |
| $V_{EB(off)} = 1.5\text{ V}; V_{CE} = 80\text{ V}; T_C = 150^\circ\text{C}$ | I_{CEX} | max. | - | - 5.0 mA |
| Emitter cut-off current | | | | |
| $I_C = 0; V_{EB} = 5\text{ V}$ | I_{EBO} | max. | 1.0 | mA |
| Breakdown voltages | | | | |
| $I_C = 200\text{ mA}; I_B = 0$ | $V_{CEO(sus)}^*$ | min. | 40 | 60 80 V |
| $I_C = 1\text{ mA}; I_E = 0$ | V_{CBO} | min. | 50 | 70 90 V |
| $I_C = 200\text{ mA}; V_{BE} = 1.5\text{ V}$ | $V_{CEX(sus)}^*$ | min. | 50 | 70 90 V |
| $I_E = 1\text{ mA}; I_C = 0$ | V_{EBO} | min. | | 5.0 V |
| Saturation voltages | | | | |
| $I_C = 5\text{ A}; I_B = 0.5\text{ A}$ | V_{CEsat}^* | max. | 1.3 | V |
| $I_C = 15\text{ A}; I_B = 5\text{ A}$ | V_{CEsat}^* | max. | 3.5 | V |
| Base-emitter on voltage | | | | |
| $I_C = 5\text{ A}; V_{CE} = 4\text{ V}$ | $V_{BE(on)}^*$ | max. | 1.3 | V |
| $I_C = 15\text{ A}; V_{CE} = 4\text{ V}$ | $V_{BE(on)}^*$ | max. | 3.5 | V |
| D.C. current gain | | | | |
| $I_C = 5\text{ A}; V_{CE} = 4\text{ V}$ | h_{FE}^* | min. | 20 | |
| | | max. | 150 | |
| $I_C = 15\text{ A}; V_{CE} = 4\text{ V}$ | h_{FE}^* | min. | 5.0 | |
| Transition frequency | | | | |
| $I_C = 1\text{ A}; V_{CE} = 4\text{ V}; f = 1\text{ MHz}$ | $f_T(1)$ | min. | 5.0 | MHz |
| Small signal current gain | | | | |
| $I_C = 1.0\text{ A}; V_{CE} = 4\text{ V}; f = 1.0\text{ KHz}$ | h_{fe} | min. | 25 | |

* Pulse test: pulse width $\leq 300\ \mu\text{s}$; duty cycle $\leq 2\%$

(1) $f_T = |h_{fe}| \cdot f_{test}$

Notes

Disclaimer

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